

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 198092US-2S DIV	SERIAL NO. New Divisional Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Hironobu KON et al	
		FILING DATE Herewith	GROUP 2814

76-09684-04  
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TT	AA	5,729,032	03/1998	TOMOMATSU ET AL			
TT	AB	5,610,439	03/11/97	HIYOSHI ET AL			
TT	AC	5,530,277	06/1996	OTSUKI ET AL			
TT	AD	5,448,083	09/05/95	KITAGAWA ET AL			
TT	AE	5,329,142	07/12/94	KITAGAWA ET AL			
	AF						
	AG						
	AH						
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	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	NO
	AO	44 29733 A1	3/1995	GERMANY (with abstract)		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

TT	AW	Hideo Matsuda, "Pressure Contact Assembly Technology of High Power Devices," Power Semiconductor Devices and ICs, 1997. ISPSD '97 1997 IEEE International Symposium on, May 1997, pp. 17-24.
TT	AX	M. Kudoh, et al., "Current Sensing IGBT for Future Intelligent Power Module," Power Semiconductor Devices and ICs, 1996. ISPSD '96 Proceedings.,8th International Symposium on, May 1996, pp. 303-306.
TT	AY	Mitsuhiko Kitagawa, et al., "A 4500V Injection Enhanced Insulated Gate Bipolar Transistor (IEGT) Operating in a Mode Similar to a Thyristor," IEDM, December 1993, pp. 679-682.
TT	AZ	Noriyuki Iwamuro, "A New Vertical IGBT Structure with a Monolithic Over-Current, Over-Voltage, and Over-Temperature Sensing and Protecting Circuit," IEEE Electron Device Lett., Vol. 16, No. 9, September 1995, pp. 399-401.

Examiner	<i>[Signature]</i>	Date Considered <i>10/02/01</i>
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\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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TT	AAA	Yasukazu Seki, et al., "A New IGBT with a Monolithic Over-Current Protection Circuit," Proc. of the 6 <sup>th</sup> Internat. Symposium on Power Semiconductor Davos, Switzerland, May 31-June 2, 1994, pp. 31-35.			
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	AAQ				
Examiner		<i>Wark</i>		Date Considered 10/02/01	

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